HEF4082B

Dual 4-input AND gate

Rev. 5 — 16 November 2011

Product data sheet

1. General description

The HEF4082B is a dual 4-input AND gate. The outputs are fully buffered for highest noise immunity and pattern insensitivity to output impedance variations.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

2. Features and benefits

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Inputs and outputs are protected against electrostatic effects
- Specified from -40 °C to +85 °C and -40 °C to +125 °C
- Complies with JEDEC standard JESD 13-B

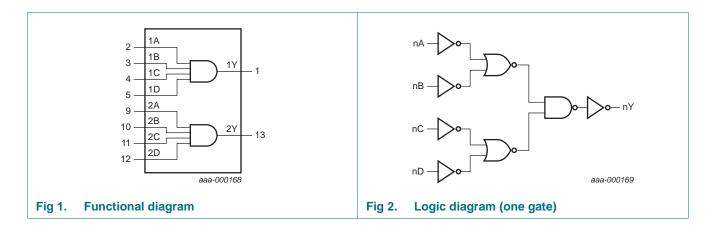
3. Ordering information

Table 1. Ordering information

All types operate from $-40~^{\circ}\text{C}$ to $+125~^{\circ}\text{C}$.

Type number	Package									
	Name	Description	Version							
HEF4082BP	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1							
HEF4082BT	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1							

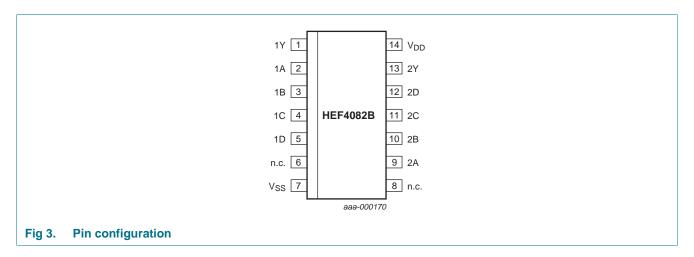
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A, 1B, 1C, 1D	2, 3, 4, 5	input
2A, 2B, 2C, 2D	9, 10, 11, 12	input
1Y, 2Y	1, 13	output
n.c.	6, 8	not connected
V _{SS}	7	ground (0 V)
V_{DD}	14	supply voltage

6. Functional description

Table 3. Function table [1]

Input	nput								
nA	nB	nC	nD	nY					
L	X	X	X	L					
X	L	Χ	X	L					
X	Χ	L	X	L					
X	Χ	Χ	L	L					
Н	Н	Н	Н	Н					

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to V_{SS} = 0 V (ground).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$	-	±10	mA
I _{I/O}	input/output current		-	±10	mA
I_{DD}	supply current		-	50	mA
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		-40	+125	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to + 125 } ^{\circ}\text{C}$			
		DIP14	<u>[1]</u> _	750	mW
		SO14	[2] _	500	mW
Р	power dissipation	per output	-	100	mW

^[1] For DIP14 packages: above T_{amb} = 70 °C, P_{tot} derates linearly with 12 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		3	15	V
V_{I}	input voltage		0	V_{DD}	V
T _{amb}	ambient temperature	in free air	-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5 V$	-	3.75	ns/V
		V _{DD} = 10 V	-	0.5	ns/V
		V _{DD} = 15 V	-	0.08	ns/V

9. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0$ V; $V_{I} = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	T _{amb} = -40 °C		T _{amb} = +25 °C		T _{amb} = +85 °C		+125 °C	Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
	HIGH-level	I _O < 1 μA	5 V	3.5	-	3.5	-	3.5	-	3.5	-	V
	input voltage		10 V	7.0	-	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level	I _O < 1 μA	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V
	input voltage		10 V	-	3.0	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V

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^[2] For SO14 packages: above T_{amb} = 70 °C, P_{tot} derates linearly with 8 mW/K.

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 Table 6.
 Static characteristics ...continued

 $V_{SS} = 0 \ V$; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	–40 °C	T _{amb} =	+25 °C	T _{amb} =	+85 °C	T _{amb} =	+125 °C	Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V_{OH}	HIGH-level output voltage	$ I_{O} < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level	$ I_O < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level output current	$V_0 = 2.5 \text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	-	-1.1	mA
		V _O = 4.6 V	5 V	-	-0.64	-	-0.5	-	-0.36	-	-0.36	mΑ
		V _O = 9.5 V	10 V	-	-1.6	-	-1.3	-	-0.9	-	-0.9	mA
		V _O = 13.5 V	15 V	-	-4.2	-	-3.4	-	-2.4	-	-2.4	mA
I _{OL}	LOW-level	$V_0 = 0.4 \ V$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA
	output current	$V_0 = 0.5 \text{ V}$	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA
		V _O = 1.5 V	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mA
I _I	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μА
I_{DD}	supply current	all valid input	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μΑ
		combinations; $I_0 = 0 A$	10 V	-	0.5	-	0.5	-	15.0	-	15.0	μΑ
			15 V	-	1.0	-	1.0	-	30.0	-	30.0	μΑ
C _I	input capacitance			-	-	-	7.5	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $T_{amb} = 25$ °C; $C_L = 50$ pF; $t_r = t_f \le 20$ ns; waveforms see Figure 4; test circuit see Figure 5; unless otherwise specified.

G1112		,					•	
Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Тур	Max	Unit
t _{pd}	propagation delay	nA, nB, nC,	5 V	[2] $38 + 0.55 \times C_L$	-	65	125	ns
		nD to nY	10 V	19 + 0.23 × C _L	-	30	60	ns
			15 V	17 + 0.16 × C _L	-	25	45	ns
	HIGH to LOW output	nY	5 V	$10 + 1.0 \times C_L$	-	60	120	ns
	transition time		10 V	$9 + 0.42 \times C_L$	-	30	60	ns
			15 V	$6 + 0.28 \times C_L$	-	20	40	ns
t _{TLH}	LOW to HIGH output	nY	5 V	$10 + 1.0 \times C_L$	-	60	120	ns
	transition time	10		$9 + 0.42 \times C_L$	-	30	60	ns
		1	15 V	$6 + 0.28 \times C_L$	-	20	40	ns

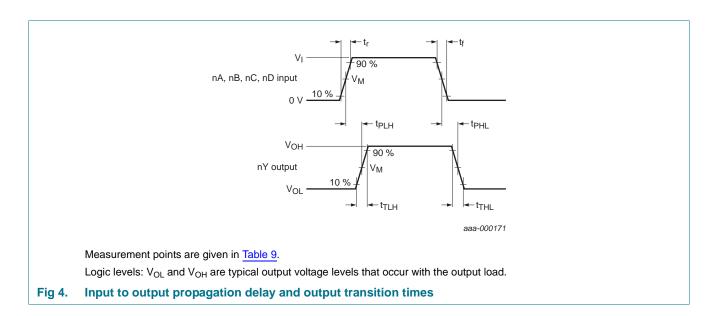
^[1] The typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C_L in pF).

Table 8. Dynamic power dissipation

 $V_{SS} = 0 \text{ V; } t_r = t_f \le 20 \text{ ns; } T_{amb} = 25 \text{ °C.}$

Symbol	Parameter	V_{DD}	Typical formula	where:
P_D	dynamic power dissipation	5 V	$P_D = 1500 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	f_i = input frequency in MHz;
		10 V	$P_D = 6700 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	fo = output frequency in MHz;
		15 V	$P_D = 16800 \times f_i + \Sigma (f_0 \times C_L) \times V_{DD}^2 (\mu W)$	C_L = output load capacitance in pF;
				$\Sigma(f_0 \times C_L)$ = sum of the outputs;
				V _{DD} = supply voltage in V.

11. Waveforms



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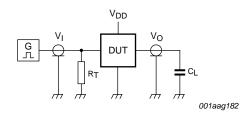
^[2] t_{pd} is the same as t_{PHL} and t_{PLH} .

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Table 9. Measurement points

Supply voltage	Input	Output
V_{DD}	V _M	V _M
5 V to 15 V	0.5V _{DD}	0.5V _{DD}



Test data is given in Table 10.

Definitions for test circuit:

DUT = Device Under Test.

 C_L = load capacitance including jig and probe capacitance.

 R_T = termination resistance should be equal to the output impedance Z_0 of the pulse generator.

Fig 5. Test circuit

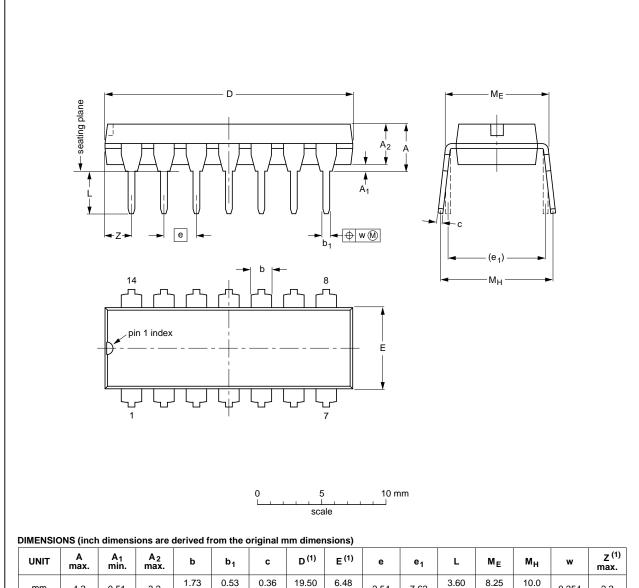
Table 10. Test data

Supply voltage	Input	Load	
V_{DD}	VI	t _r , t _f	CL
5 V to 15 V	V _{SS} or V _{DD}	≤ 20 ns	50 pF

12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

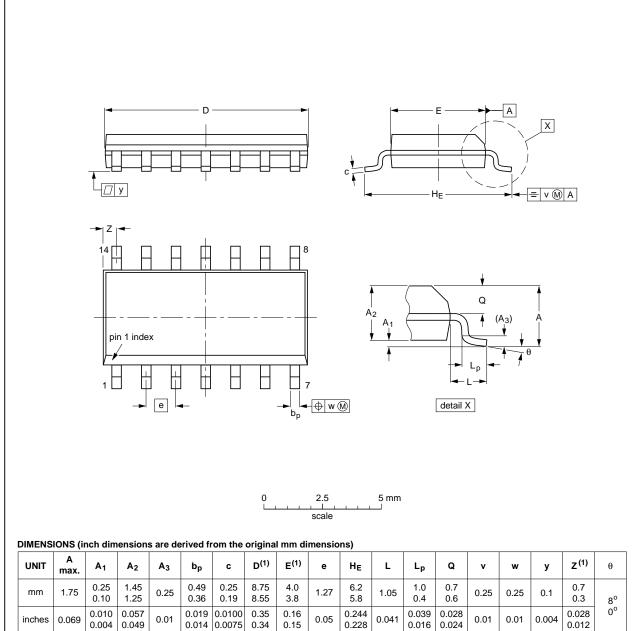
OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT27-1	050G04	MO-001	SC-501-14			99-12-27 03-02-13
	•					

Fig 6. Package outline SOT27-1 (DIP14)

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



inches

Note 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.0075

0.34

0.15

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				99-12-27 03-02-19

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Package outline SOT108-1 (SO14) Fig 7.

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13. Abbreviations

Table 11. Abbreviations

Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4082B v.5	20111116	Product data sheet	-	HEF4082B v.4
Modifications:	Legal pagesChanges in	updated. "General description" and "Fe	atures and benefits".	
HEF4082B v.4	20110823	Product data sheet	-	HEF4082B_CNV v.3
HEF4082B_CNV v.3	19950101	Product specification	-	HEF4082B_CNV v.2
HEF4082B_CNV v.2	19950101	Product specification	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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